

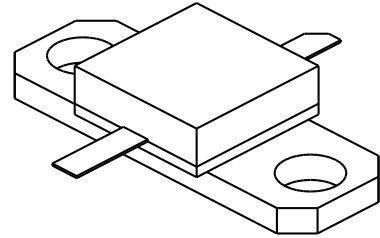
# TAN15

15 Watts, 40 Volts, Pulsed  
Avionics 960 - 1215 MHz

## GENERAL DESCRIPTION

The TAN15 is a COMMON BASE bipolar transistor. It is designed for pulsed systems in the frequency band 960-1215 MHz. The device has gold thin-film metallization and diffused ballasting for proven highest MTF. The transistor includes input prematch for broadband capability. Low thermal resistance package reduces junction temperature, extends life.

## CASE OUTLINE 55LT, STYLE 1



## ABSOLUTE MAXIMUM RATINGS

|   |                 |
|---|-----------------|
| Maximum Power Dissipation @ 25°C <sup>2</sup> | 175 Watts       |
| <b>Maximum Voltage and Current</b>            |                 |
| BVces Collector to Base Voltage               | 50 Volts        |
| BVebo Emitter to Base Voltage                 | 4.0 Volts       |
| Ic <sup>2</sup> Collector Current             | 2.0 Amps        |
| <b>Maximum Temperatures</b>                   |                 |
| Storage Temperature                           | - 65 to + 150°C |
| Operating Junction Temperature                | + 200°C         |

## ELECTRICAL CHARACTERISTICS @ 25 °C

| SYMBOL | CHARACTERISTICS         | TEST CONDITIONS  | MIN | TYP | MAX  | UNITS |
|--------|-------------------------|------------------|-----|-----|------|-------|
| Pout   | Power Out               | F = 960-1215 MHz | 15  |     |      | Watts |
| Pin    | Power Input             | Vcc = 40 Volts   |     |     | 3.0  | Watts |
| Pg     | Power Gain              | PW = 20 μsec     | 7.0 | 8.0 |      | dB    |
| ηc     | Collector Efficiency    | DF = 5%          |     | 40  |      | %     |
| VSWR   | Load Mismatch Tolerance | F = 1090 MHz     |     |     | 10:1 |       |

|                  |                                |                       |     |  |     |       |
|------------------|--------------------------------|-----------------------|-----|--|-----|-------|
| BVebo            | Emitter to Base Breakdown      | Ie = 5 mA             | 3.5 |  |     | Volts |
| BVces            | Collector to Emitter Breakdown | Ic = 10 mA            | 50  |  |     | Volts |
| hFE              | DC - Current Gain              | Ic = 10 mA, Vce = 5 V |     |  | 1.0 | °C/W  |
| θjc <sup>2</sup> | Thermal Resistance             |                       |     |  |     |       |

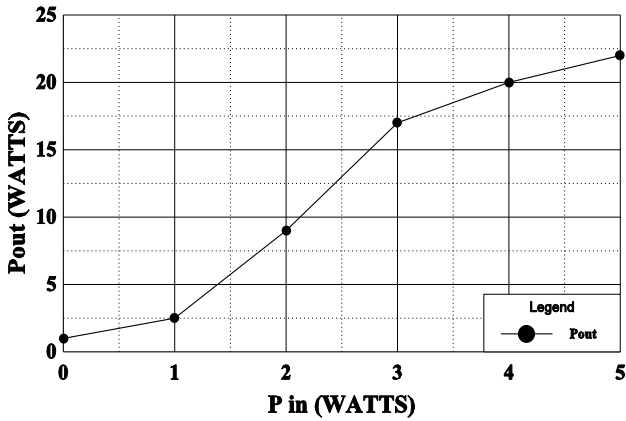
- Note 1: At rated output power and pulse conditions  
2: At rated pulse conditions

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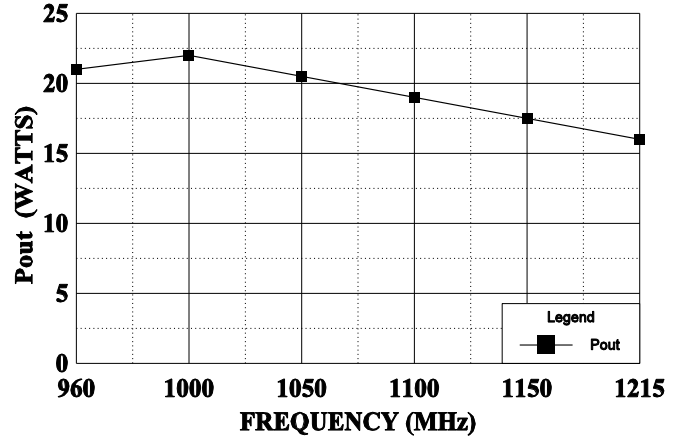
**POWER OUTPUT vs POWER INPUT**

Vcc = 40 V, 1090 MHz



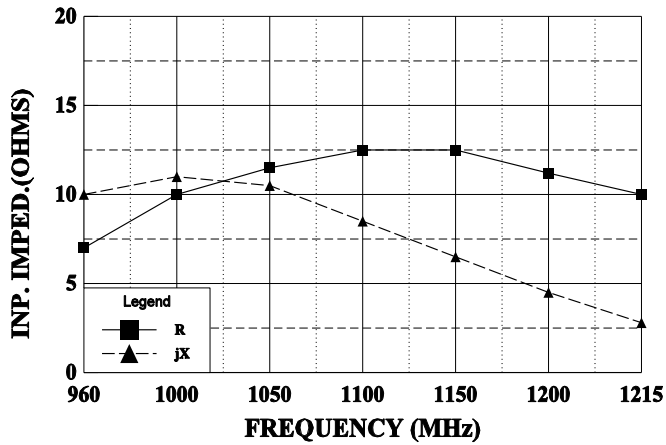
**POWER OUTPUT VS FREQUENCY**

Vcc = 40V, Pin = 3.0 W



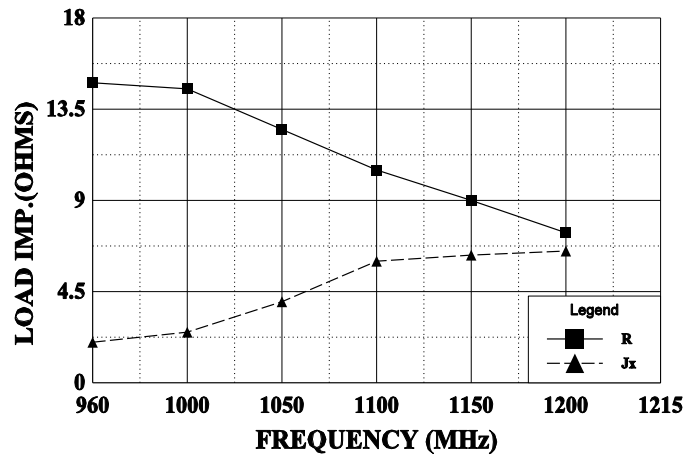
**SERIES INPUT IMPEDANCE vs FREQUENCY**

Vcc = 40 V, Pin = 15 W



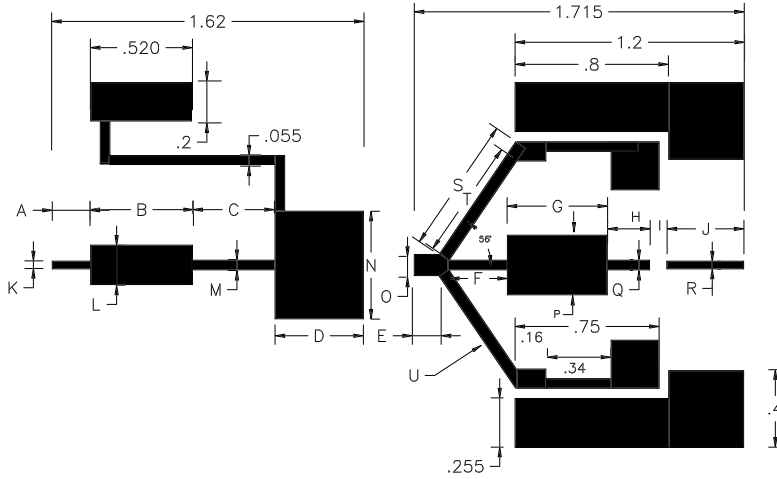
**SERIES LOAD IMPEDANCE vs FREQUENCY**

Vcc = 40 V, Po = 15 W



REVISIONS

| ZONE | REV | DESCRIPTION | DATE | APPROVED |
|------|-----|-------------|------|----------|
|------|-----|-------------|------|----------|



| DIM | INCHES |
|-----|--------|
| A   | .200   |
| B   | .530   |
| C   | .430   |
| D   | .460   |
| E   | .125   |
| F   | .300   |
| G   | .520   |
| H   | .240   |
| I   | .070   |
| J   | .400   |
| K   | .040   |
| L   | .205   |
| M   | .050   |
| N   | .560   |
| O   | .110   |
| P   | .310   |
| Q   | .050   |
| R   | .040   |
| S   | .710   |
| T   | .610   |
| U   | .060   |

TAN 15 TEST CIRCUIT

file:tan15ckt.dwg 8/17/95 jc

DIELECTRIC = 15 MIL THICK TFE Er = 2.55



|               |                   |          |
|---------------|-------------------|----------|
| CAGE<br>OPJR2 | DWG NO.<br>TAN 15 | REV<br>— |
| SCALE<br>1/1  | SHEET             |          |